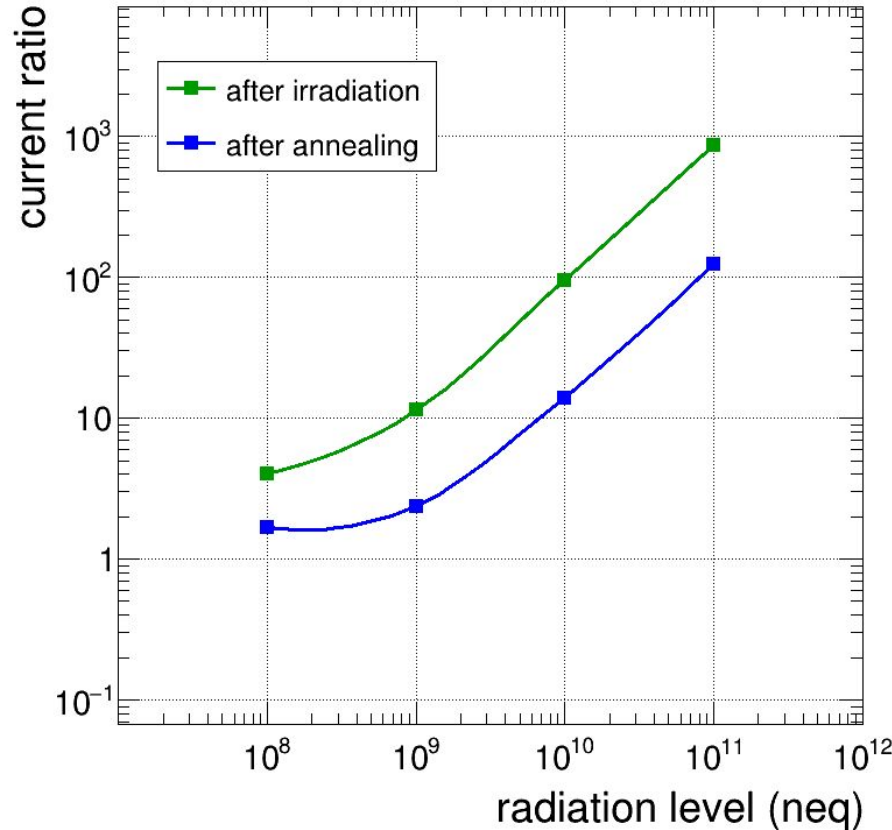


[NUV-HD-RH] 1 week of annealing at T = 125 C



annealing reduced dark current by a factor of ~5-10, in line with expectations

SiPM irradiated up to 10^{11} now behave like if they were irradiated by 10^{10}

for the time being we stop here with FBK sensors, or perhaps we extend annealing at T = 125 C for another 2 weeks (expecting no improvements)

issue with FBK carriers related to the solder paste used during assembly, unfortunately we have used low-T (138 C) solder paste which does not allow to reach the ultimate annealing temperature of T = 175 \rightarrow needs reworking of the carriers \rightarrow will be done after test beam

T = 20 C
 $V_{\text{bias}} = 33$ V